

Title (en)

ACCELERATION OF THE PROGRAMMING OF A MEMORY MODULE WITH THE AID OF A BOUNDARY SCAN (BSCAN) REGISTER

Title (de)

BESCHLEUNIGUNG DER PROGRAMMIERUNG EINES SPEICHERBAUSTEINS MIT HILFE EINES BOUNDARY SCAN (BSCAN)-REGISTERS

Title (fr)

ACCELERATION DE LA PROGRAMMATION D'UN MODULE DE MEMOIRE A L'AIDE D'UN REGISTRE A DECALAGE PERIPHERIQUE (BSCAN)

Publication

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Application

**EP 03798062 A 20030903**

Priority

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Abstract (en)

[origin: WO2004029982A2] In order to program a memory module (104), some of its inputs (CS, OE, WR, ADDR, DATA) are stimulated via internal memory locations (103) of a so-called boundary scan (BSCAN) register (102) that is provided in the form of an IC or ASIC. In order to activate or deactivate a write operation, the control signal input (WR) of the memory module (104), said control signal input being responsible for generating a WRITE\_ENABLE signal (301d), is controlled exclusively. The switching over of the WRITE\_ENABLE signal (301d) from "LOW" to "HIGH" potential and vice versa thus ensues according to two JTAG instructions (WR\_L, WR\_H) of an instruction sequence (301a) that provides for the generation of a LOW or HIGH level at the setting signal input or resetting signal input of an update flip-flop (108) of the memory location (103) responsible for generating the WRITE\_ENABLE signal. By appropriately modifying the control unit (106) and the BSCAN cell (103), which stimulates the WRITE\_ENABLE signal (301d) at the WR input of the memory module (104), the programming can be accelerated without having to expand the interface between the control unit (106) and the BSCAN register (102) to the board and equipment level. In another embodiment of the invention, a control unit (106) automatically switches over the WRITE\_ENABLE signal (301d) from "LOW" to "HIGH" potential or from HIGH to LOW potential at an appropriate or rather programmable point in time by setting or resetting the update flip-flop (108) of the memory location (103) responsible for generating the WRITE\_ENABLE signal.

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IPC 8 full level

**G11C 29/30** (2006.01)

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